NPN Epitaxial Planar Silicon Transistor



2SC4480

Low-Frequency General-Purpose Amplifier, General Driver Applications

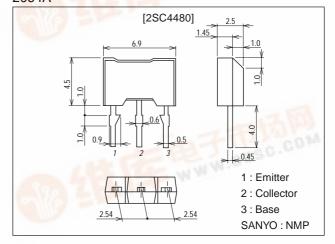
Features

- · Large current capacity.
- · Adoption of MBIT process.
- · High DC current gain.
- · Low collector-to-emitter saturation voltage.
- · High V_{EBO}.

Package Dimensions

unit:mm

2064A



Specifications

Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V _{CBO}		30	V
Collector-to-Emitter Voltage	V _{CEO}		25	V
Emitter-to-Base Voltage	V _{EBO}	pal.	15	V
Collector Current	l _C	Same CE	2	Α
Collector Current (Pulse)	ICP	The Colonial Park	4	Α
Base Current	IB	A STATE OF WAR	0.4	Α
Collector Dissipation	PC		1	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg	- 24	-55 to +150	°C

Electrical Characteristics at Ta = 25°C

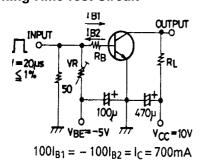
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector Cutoff Current	ICBO	V _{CB} =20V, I _E =0			100	nA
Emitter Cutoff Current	I _{EBO}	V _{EB} =10V, I _C =0		LTT	100	nA
DC Current Gain	h _{FE} 1	V _{CE} =5V, I _C =500mA	800	1500	3200	
	h _{FE} 2	V _{CE} =5V, I _C =1A	600	M.D.		
Gain-Bandwidth Product	f _T	V _{CE} =10V, I _C =50mA	A1	260		MHz
Output Capacitance	C _{ob}	V _{CB} =10V, f=1MHz		27		pF

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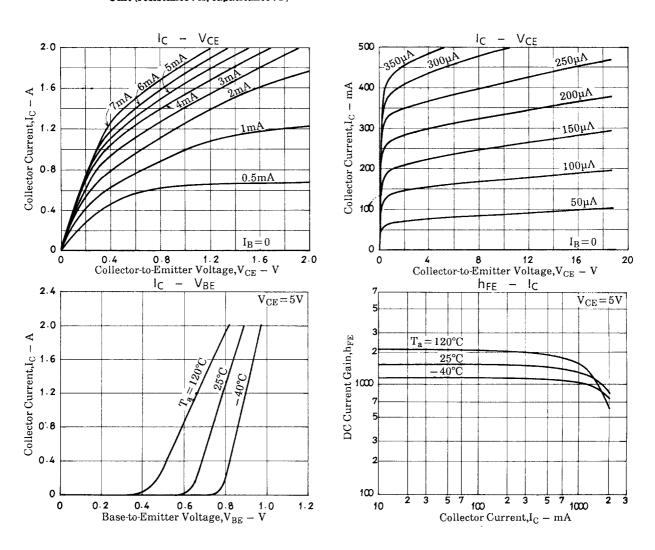
SANYO Electric Co.,Ltd. Semiconductor Bussiness Headquaters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110-8534 JAPAN

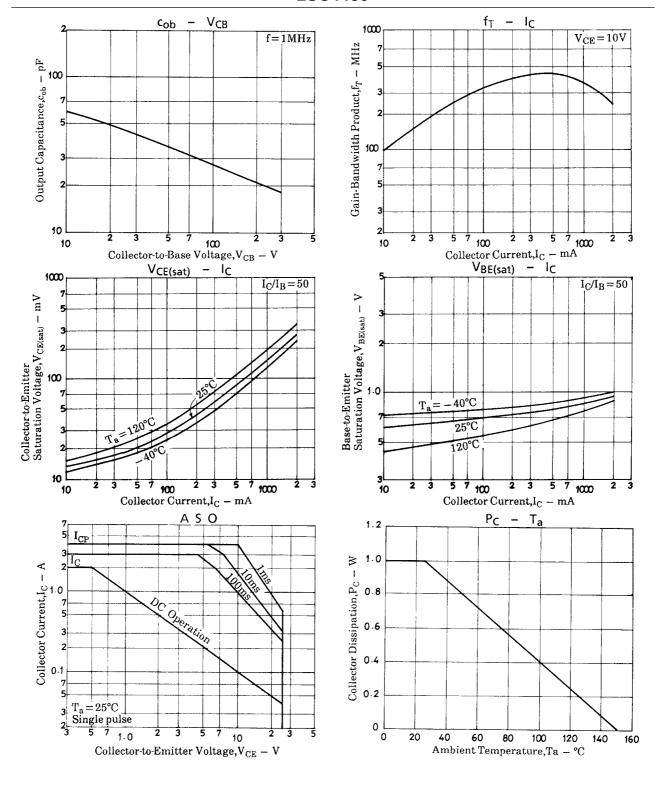
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Offic
Collector-to-Emitter Saturation Voltage	V _{CE(sat)}	I _C =1A, I _B =20mA		0.15	0.5	V
Base-to-Emitter Saturation Voltage	V _{BE(sat)}	I _C =1A, I _B =20mA		0.85	1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	$I_{C}=10\mu A, I_{E}=0$	30			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =1mA, R _{BE} =∞	25			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =10μA, I _C =0	15			V
Turn-ON Time	ton	See specified Test Circuit.		0.14		μs
Storage Time	t _{stg}	See specified Test Circuit.		1.35		μs
Fall Time	t _f	See specified Test Circuit.		0.1		μs

Switching Time Test Circuit



Unit (resistance: Ω , capacitance: F)





2SC4480

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